

PEMD20

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

29 December 2022

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in an ultra small flat lead SOT666 Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PEMH20 PNP/PNP complement: PEMB20

2. Features and benefits

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	er transistor; for the PNP transistor with negative polarity						
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
lo	output current			-	-	100	mA
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[1]	0.8	1	1.2	

[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R1
6	01	output (collector) TR1	1 2 3	
			SOT666	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage						
	Name	Description	Version					
PEMD20	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	<u>SOT666</u>					

7. Marking

Table 4. Marking codes

Type number	Marking code
PEMD20	6н

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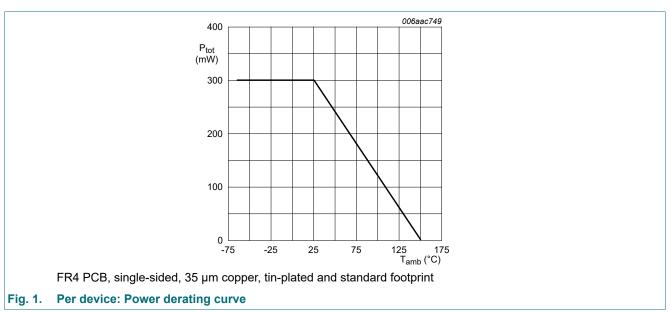
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
for the PNP transistor wit	h negative polarity	'	'		
collector-base voltage	open emitter		-	50	V
collector-emitter voltage	open base		-	50	V
emitter-base voltage	open collector		-	10	V
output current			-	100	mA
total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
		'			
input voltage	positive		-	12	V
	negative		-	-10	V
input voltage	positive		-	10	V
	negative		-	-12	V
total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
junction temperature			-	150	°C
ambient temperature			-65	150	°C
storage temperature			-65	150	°C
	for the PNP transistor with collector-base voltage collector-emitter voltage emitter-base voltage output current total power dissipation input voltage input voltage total power dissipation junction temperature ambient temperature	for the PNP transistor with negative polarity collector-base voltage open emitter collector-emitter voltage open base emitter-base voltage open collector output current total power dissipation T _{amb} ≤ 25 °C input voltage positive negative total power dissipation T _{amb} ≤ 25 °C total power dissipation T _{amb} ≤ 25 °C input voltage positive negative total power dissipation T _{amb} ≤ 25 °C junction temperature ambient temperature	for the PNP transistor with negative polarity collector-base voltage open emitter collector-emitter voltage open base emitter-base voltage open collector output current total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ [1] input voltage positive negative input voltage positive negative total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ [1] total power dissipation $T_{amb} \le 25 ^{\circ}\text{C}$ [1] input voltage positive negative	for the PNP transistor with negative polarity collector-base voltage open emitter - collector-emitter voltage open base - emitter-base voltage open collector - output current - - total power dissipation $T_{amb} \le 25 ^{\circ}$ C [1] - input voltage positive - negative - - total power dissipation $T_{amb} \le 25 ^{\circ}$ C [1] - junction temperature - - ambient temperature - -	for the PNP transistor with negative polarity collector-base voltage open emitter - 50 collector-emitter voltage open base - 50 emitter-base voltage open collector - 10 output current - 100 total power dissipation $T_{amb} \le 25 ^{\circ}$ C [1] - 200 input voltage positive - 12 negative 10 input voltage positive 10 total power dissipation $T_{amb} \le 25 ^{\circ}$ C [1] - 300 junction temperature - 150 ambient temperature - 65 150

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

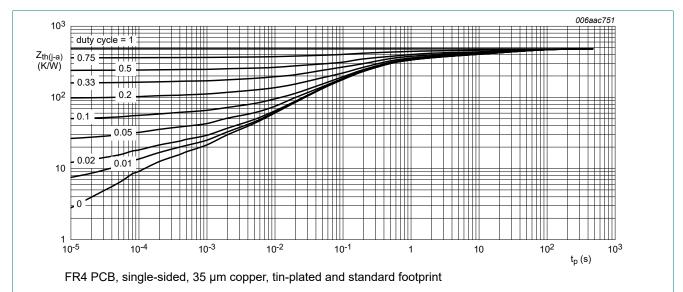


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

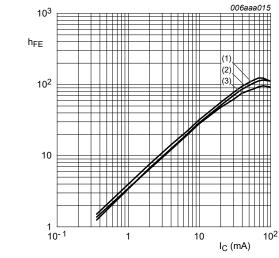
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or; for the PNP transistor	with negative polarity					
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \mu A; I_E = 0 A; T_{amb} = 25 °C$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I _{CEO} collector-emitter cut-o	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ	
current		V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	2	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C		-	1.2	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA; T _{amb} = 25 °C		2	1.6	-	V
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[1]	0.8	1	1.2	
TR1 (NPN)			'				
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	2.5	pF
TR2 (PNP)			•		•		
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	3	pF

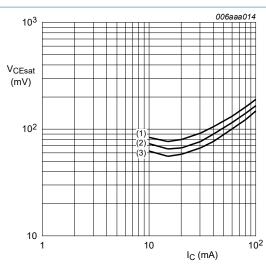
^[1] See section "Test information" for resistor calculation and test conditions.

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω



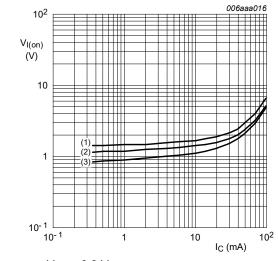
V_{CE} = 5 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



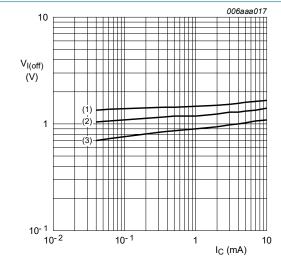
 $V_{CE} = 0.3 V$

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$

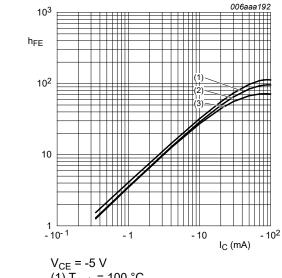
(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

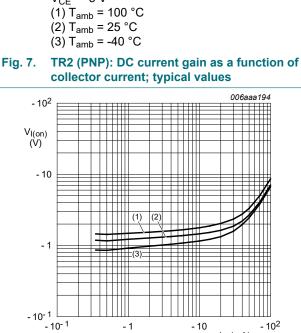
(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω



collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

$$(1) T_{amb} = -40 °C$$

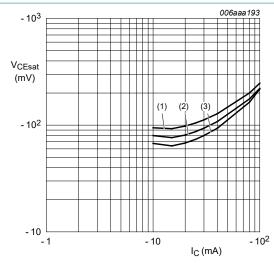
- 1

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 9. of collector current; typical values

- 10



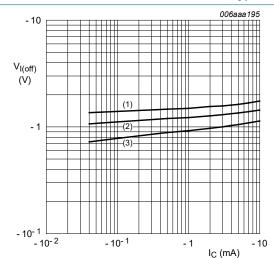
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 100 \, ^{\circ}C$
(2) $T_{amb} = 25 \, ^{\circ}C$
(3) $T_{amb} = -40 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE}$$
 = -5 V

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

- 10²

I_C (mA)

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

11. Test information

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I3)}{R1 \cdot I3} - 1$$

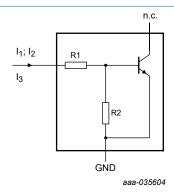


Fig. 11. TR1 (NPN): Resistor test circuit

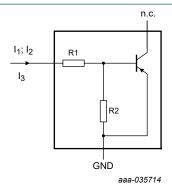


Fig. 12. TR2 (PNP): Resistor test circuit

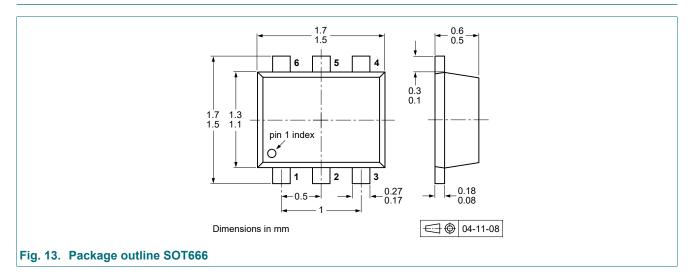
Resistor test conditions

Table 8. Resistor test conditions

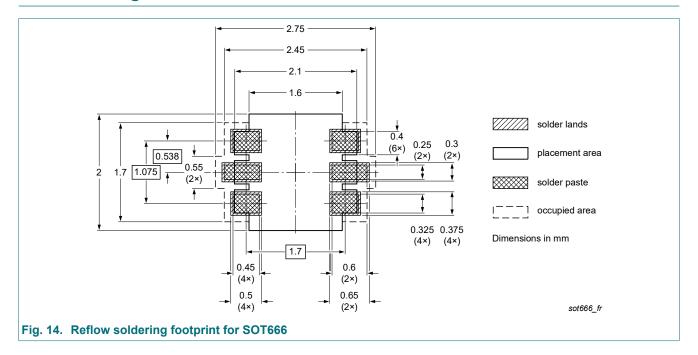
PEMD20	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃		
TR1 (NPN)	2.2	2.2	750 μΑ	950 μΑ	-850 μΑ		
TR2 (PNP)	2.2	2.2	-750 μΑ	-950 μΑ	850 μΑ		

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

12. Package outline



13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PEMD20 v.2	20221229	Product data sheet	-	PEMD20_PUMD20_1
Modifications:	guidelines of Legal texts ha Family data s Section "Pac	Nexperia.	he new com type data sl oved.	
PEMD20_PUMD20_1	20050502	Product data sheet	-	-

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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Contents

1.	General description	1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	. 3
9.	Thermal characteristics	. 4
10.	Characteristics	5
11.	Test information	8
12.	Package outline	. 9
13.	Soldering	. 9
14.	Revision history	10
	Legal information	

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12 / 12

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